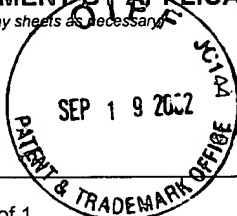


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Sheet 1 of 1

Complete if Known

Application Number	09/483881
Filing Date	January 18, 2000
First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Unknown

Attorney Docket No: 00303.672US1

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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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10-19-02

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